Salahaddin University-Erbil
Science College
3rd Year Medical Physics

Sub.: Applied Electronics
Date:
Time:

Q1/ Draw a "Light-Activated Circuit" using a photoresistor as the sensor element for light.

Q2/ Determine $\mathrm{V}_{\text {out }}$ In the following circuit.


Q3/ Draw a circuit of op-amp "RC Relaxation Oscillators" and explain it briefly.

Q4/Explain the basic components of any "Voltage Regulators" circuit.

Q5/ Given $\mathrm{VCC}=+15 \mathrm{~V}, \mathrm{VB}=5.6 \mathrm{~V}, \mathrm{R} 1=4.7 \mathrm{k} \Omega$, $R 2=3.3 \mathrm{k} \Omega$, and $\mathrm{hFE}=100$, find $\mathrm{VE}, \mathrm{IE}, \mathrm{IB}, \mathrm{IC}$, and VC .


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Q6/ Solve for the gain (Vout/Vin) of the circuit below, then find the value of the voltage gain.


Q7/ If VGS, off $=-4 \mathrm{~V}$ and IDSS $=12 \mathrm{~mA}$, find the values of ID and gm and RDS when VGS=-2 V and when $\mathrm{VGS}=+1 \mathrm{~V}$ Assume that the JFET is in the active region.

Q8/ Draw and explain "ASTABLE MULTIVIBRATOR" transistor circuit.


Q9/ Solve for Vout in terms of Vin.


Q10/ Explain the basic configuration and function of "The 555 Timer IC".

Q11/ For the following "EMITTER-FOLLOWER AMPLIFIER" circuit, [Rload $=3 \mathrm{k} \Omega, \mathrm{VCC}=+20 \mathrm{~V}$, $\beta=100, f=100 \mathrm{~Hz}$. Find RE, R1, R2, Rin(base,dc), Rin(base, ac), C1, C2.


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Q12/ For the following "common-emitter amplifier" circuit, [voltage gain $=-100$, an $\boldsymbol{f}=100 \mathrm{~Hz}$, and a quiescent current $\mathrm{IQ}=1$ $m A$, where $\beta=100$ and $V C C=10 \mathrm{~V}$ ]. Find RE, R1, R2, Rin(base,dc), Rin(base,ac), C1, C2.


Q13/Write 5 notes technical about "non-original phone chargers" available in the market.

Q14/ Draw the characteristic curve of JFET transistor.

Q15/ An $n$-channel depletion-type MOSFET has an IDDS $=10$ $m A$ and a $V G S$, off $=-4 V$. Find the values of $I D, g m$, and $R D S$ when VGS $=-2 \mathrm{~V}$. Assume that the MOSFET is in the active region.

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+V_{D D}
$$

